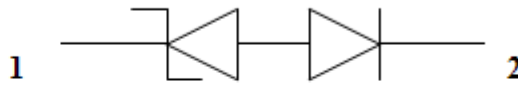
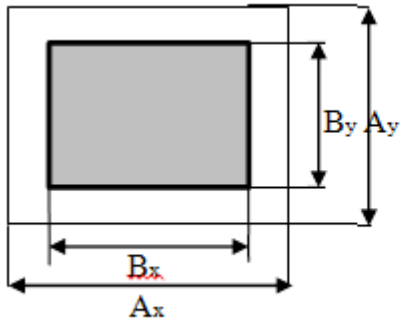




SM-3.3V3

Chip TVS diode.



Mechanical data: Ax= Ay=590 um
Bx=By=350um

Chip thickness: 138 +/-12um

Scribe Line width - 60um

Top side - pin1. Al metallization for wire bond

Back side - pin2. Ti-Ni-Ag for soldering

Schematic and pinning diagram.

Limiting values

Parameter	Symbol	Conditions	Value	Unit
Peak Pulse Power	P _{PP}	t _p =8/20us	480*	W
Peak Pulse Current	I _{PP}	t _p =8/20us	40,0*	A
Electrostatic discharge	VESD	IEC 61000-4-2. Level-4. Pin1 to Pin2.	+30,0-Contact. +30,0-Air.	kV
Max .junction temperature	T _j	-	+125	°C

Characteristics (T_j=25°C)

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _{rw}	Reverse Stand-off voltage		-	-	3,3	V
V _{pt}	Punch-Through Voltage.	I _{pt} =2uA	3,0**	-	-	V
V _{sb}	Snap-Back Voltage.	I _{sb} =50mA	2,8	-	4,0	V
I _r	Reverse leakage current	V _R =2,8V; "+" on pin 1	-	-	0,2	uA
C _j	Diode capacitance .	F=1MHz, V _{dc} =0V.	-	50	-	pF
V _{CL}	Clamping voltage	I _R =1A, t _p = 8/20uS I _R =10,0A, t _p =8/20uS I _R = 25,0A, t _D =8/20uS I _R = 40,0A, t _D =8/20uS	-	-	4,2* 6,0* 9,0* 12,0*	V
*- For Device testing. **- This Parameter guaranteed for Device.						